



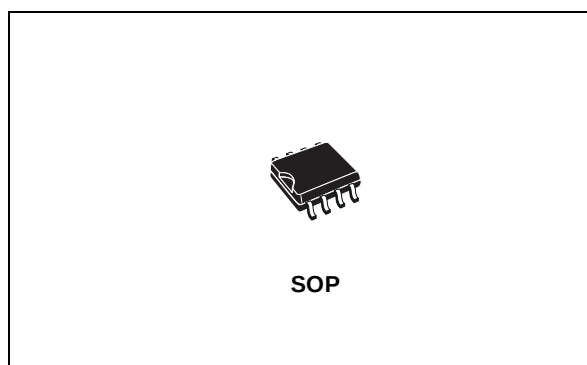
ST2042

CURRENT LIMITED POWER DISTRIBUTION SWITCHES

- 80mΩ HIGH-SIDE MOSFET SWITCH
- 500mA CONTINUOUS CURRENT PER CHANNEL
- INDEPENDENT THERMAL AND SHORT-CIRCUIT PROTECTION WITH OVERCURRENT LOGIC OUTPUT
- OPERATING RANGE FROM 2.7V TO 5.5V
- CMOS- AND TTL-COMPATIBLE ENABLE INPUTS
- 2.5ms TYPICAL RISE TIME
- UNDERVOLTAGE LOCKOUT
- 10μA MAXIMUM STANDBY SUPPLY CURRENT
- AMBIENT TEMPERATURE RANGE, 0°C TO 85°C
- ESD PROTECTION

DESCRIPTION

The ST2042 power distribution switches is intended for application where heavy capacitive loads and short circuits are likely to be encountered. These devices incorporate 80mΩ N-channel MOSFET high-side power switches for power-distribution systems that require multiple powers switches in a single package. Each switch is controlled by an independent logic enable input. Gate drive is provided by an internal charge pump designed to control the power-switch rise times and fall times to minimize current surges during



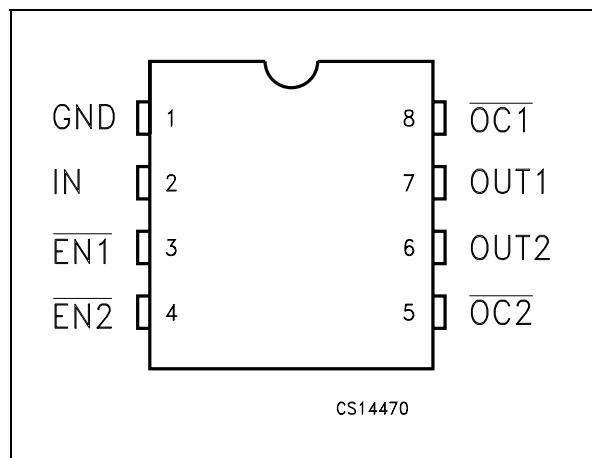
switching. The charge pump requires no external components and allows operation from supplies as low as 2.7 V.

When the output load exceeds the current-limit threshold or a short is present, these devices limit the output current to a safe level by switching into a constant-current mode, pulling the overcurrent ($\overline{OCx}$) logic output low. When continuous heavy overloads and short circuits increase the power dissipation in the switch, causing the junction temperature to rise, a thermal protection circuit shuts off the switch to prevent damage. Recovery from a thermal shutdown is automatic once the device has cooled sufficiently. Internal circuitry ensures the switch remains off until valid input voltage is present. These power-distribution switches are designed to current limit at 0.9 A

ORDERING CODES

Type	Temperature Range	Package	Comments
ST2042BD	-40 to 85 °C	SO-8 (Tube)	50parts per tube / 40tube per box
ST2042BDR	-40 to 85 °C	SO-8 (Tape & Reel)	2500 parts per reel

PIN CONFIGURATION



PIN DESCRIPTION

Pin N°	Symbol	Name And Function
1	GND	Ground
2	IN	Input Voltage
3	EN1	Enable Input. Logic Low Turns On Power Switch IN-OUT1
4	EN2	Enable Input. Logic Low Turns On Power Switch IN-OUT2
5	OC2	Overcurrent. Logic Output Active Low IN-OUT2
6	OUT2	Power Switch Output
7	OUT1	Power Switch Output
8	OC1	Overcurrent. Logic Output Active Low IN-OUT2

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_I	Input Voltage Range (Note 1)	-0.3 to 6	V
V_O	Output Voltage Range (Note 1)	-0.3 to ($V_I + 0.3$)	V
V_{IENX}	Input Voltage Range	-0.3 to 6	V
I_O	Continuous Output Current	Internally Limited	
ESD	Electrostatic Discharge	2	kV
T_J	Operating Junction Temperature	-40 to 125	°C

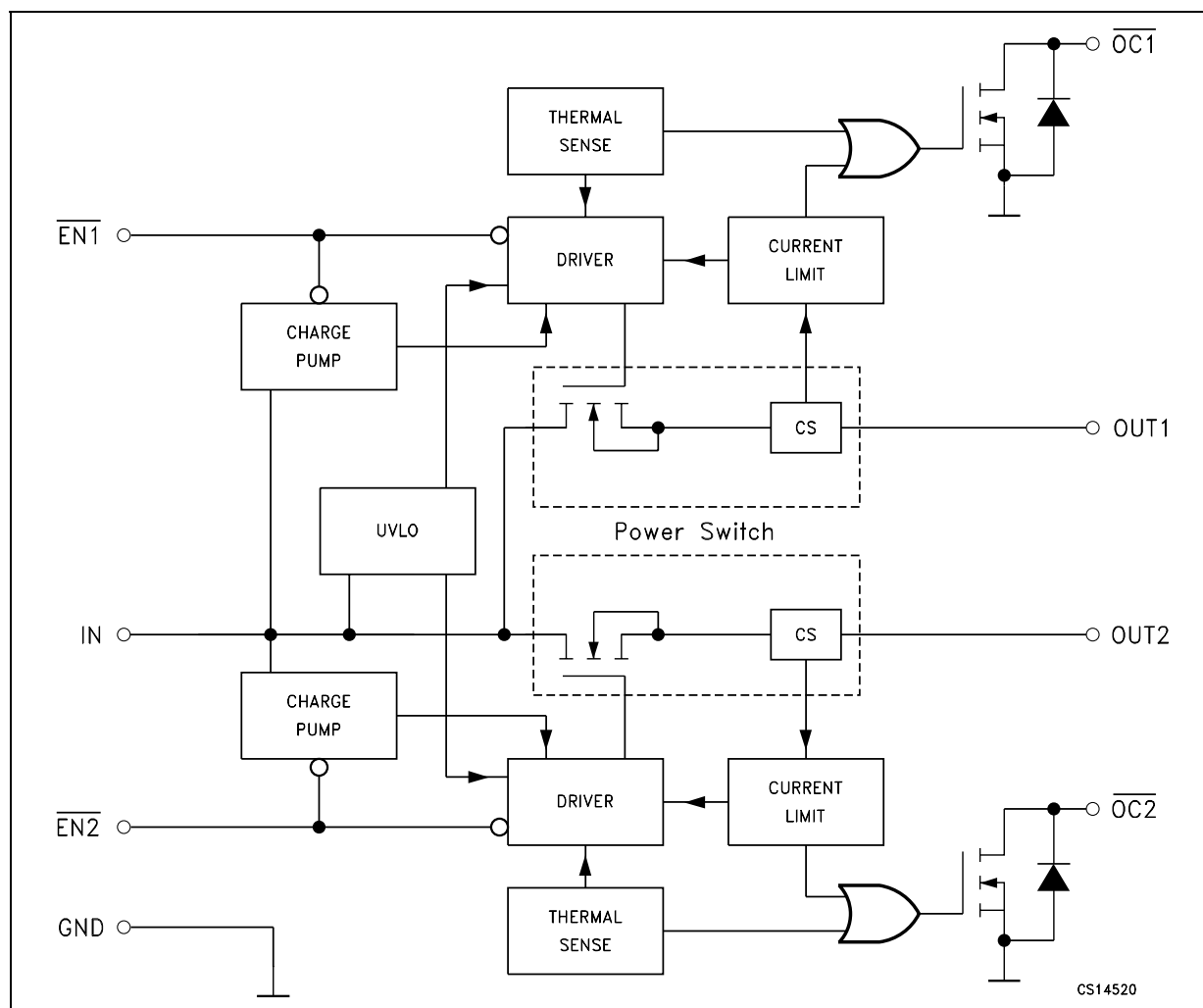
Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

Note1: All voltage are referred to GND

RECOMMENDED OPERATING CONDITION

Symbol	Parameter	Min.	Typ.	Max.	Unit
V_I	Input Voltage Range (Note 1)	2.7		5.5	V
V_O	Output Voltage Range (Note 1)	0		5.5	V
I_O	Continuous Output Current (Per Switch)	0		500	mA

BLOCK DIAGRAM



POWER SWITCH ELECTRICAL CHARACTERISTICS ($V_I = 5V$, $I_O = \text{rated current}$, $V_{\overline{IEN}} = 0V$, $T_J = 25^\circ C$, unless otherwise specified.) (See Note 1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$R_{DS(ON)}$	Static Drain-Source ON-State Resistance	$V_I = 5V$ $I_O = 0.5A$		80	100	mΩ
		$V_I = 5V$ $I_O = 0.5A$ $T_J = 85^\circ C$		90	120	
		$V_I = 5V$ $I_O = 0.5A$ $T_J = 125^\circ C$		100	135	
		$V_I = 3.3V$ $I_O = 0.5A$		90	125	
		$V_I = 3.3V$ $I_O = 0.5A$ $T_J = 85^\circ C$		110	145	
		$V_I = 3.3V$ $I_O = 0.5A$ $T_J = 125^\circ C$		120	160	
t_r	Output Rise Time	$V_I = 5.5V$ $R_L = 10\Omega$ $C_L = 1\mu F$		2.5		ms
		$V_I = 2.7V$ $R_L = 10\Omega$ $C_L = 1\mu F$		3		
t_f	Output Fall Time	$V_I = 5.5V$ $R_L = 10\Omega$ $C_L = 1\mu F$		0.3		ms
		$V_I = 2.7V$ $R_L = 10\Omega$ $C_L = 1\mu F$		0.2		

ENABLE INPUT $\overline{\text{ENx}}$ CHARACTERISTICS ($V_I = 5\text{V}$, $I_O = \text{rated current}$, $V_{\overline{\text{IEN}}} = 0\text{V}$, $T_J = 25^\circ\text{C}$, unless otherwise specified.) (See Note 1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_{IH}	High level Input Voltage	$V_I = 2.7\text{V to } 5.5\text{V}$	2			V
V_{IL}	Low level Input Voltage	$V_I = 4.5\text{V to } 5.5\text{V}$			0.8	V
		$V_I = 2.7\text{V to } 5.5\text{V}$			0.4	
I_I	Input Current	$V_{\overline{\text{IENx}}} = 0\text{V or } V_I$	-0.5		0.5	μA
t_{on}	Turn-on Time	$R_L = 10\Omega$ $C_L = 100\mu\text{F}$			20	ms
t_{off}	Turn-off Time	$R_L = 10\Omega$ $C_L = 100\mu\text{F}$			40	ms

CURRENT LIMIT CHARACTERISTICS ($V_I = 5\text{V}$, $I_O = \text{rated current}$, $V_{\overline{\text{IEN}}} = 0\text{V}$, $T_J = 25^\circ\text{C}$, unless otherwise specified.) (See Note 1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{OS}	Short Circuit Output Current	$V_I = 5\text{V}$, OUT connected to GND, device enabled into short circuit	0.7	1	1.3	A

SUPPLY CURRENT CHARACTERISTICS ($V_I = 5\text{V}$, $I_O = \text{rated current}$, $V_{\overline{\text{IEN}}} = 0\text{V}$, $T_J = 25^\circ\text{C}$, unless otherwise specified.) (See Note 1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SOL}	Current Low Level Output	$V_{\overline{\text{IENx}}} = V_I$, No Load,		0.025	1	μA
		$V_{\overline{\text{IENx}}} = V_I$, No Load, $T_J = -40 \text{ to } 125^\circ\text{C}$			10	
I_{SOH}	Current Low High Output	$V_{\overline{\text{IENx}}} = 0$, No Load,		70	90	μA
		$V_{\overline{\text{IENx}}} = 0$, No Load, $T_J = -40 \text{ to } 125^\circ\text{C}$			100	
I_L	Output Leakage Current	$V_{\overline{\text{IENx}}} = V_I$, Output Connected to GND, $T_J = -40 \text{ to } 125^\circ\text{C}$			10	μA

UNDERVOLTAGE CHARACTERISTICS ($V_I = 5\text{V}$, $I_O = \text{rated current}$, $V_{\overline{\text{IEN}}} = 0\text{V}$, $T_J = 25^\circ\text{C}$, unless otherwise specified.) (See Note 1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_{IL}	Low Level Input Voltage		2		2.5	V
V_{HYS}	Hysteresis			100		mV

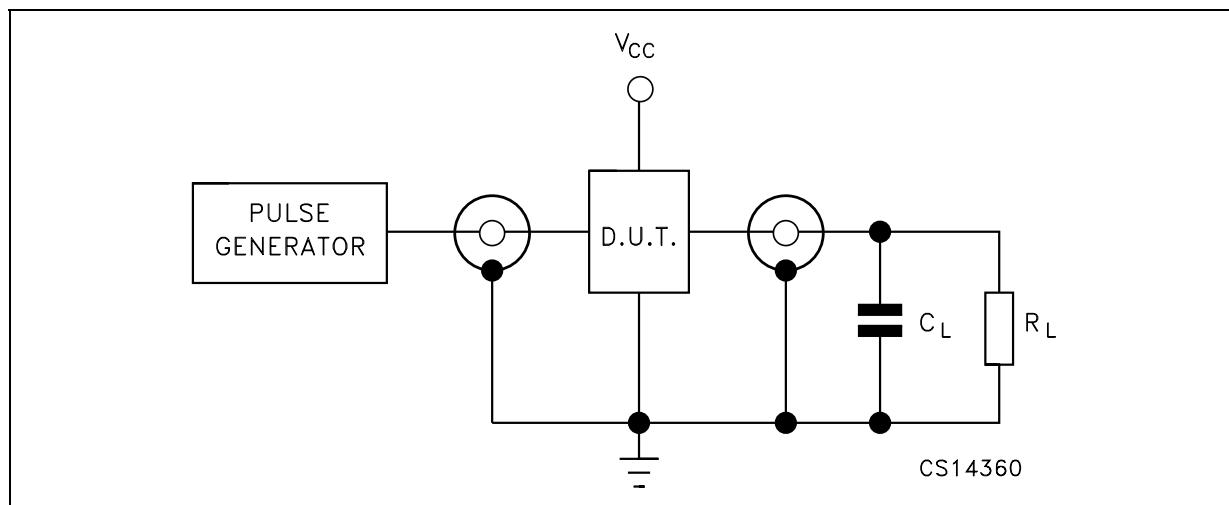
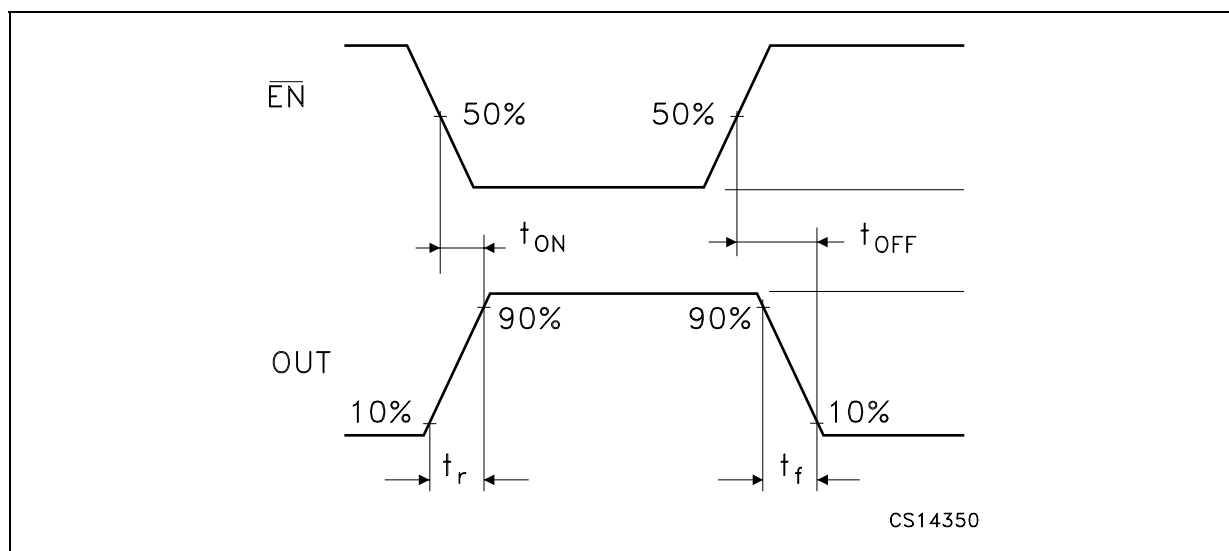
OVERCURRENT ($\overline{\text{OC}}$) CHARACTERISTICS ($V_I = 5\text{V}$, $I_O = \text{rated current}$, $V_{\overline{\text{IEN}}} = 0\text{V}$, $T_J = 25^\circ\text{C}$, unless otherwise specified.) (See Note 1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SINK}	Sink Current	$V_O = 5\text{V}$	10			mA
V_O	Output Low Voltage	$I_O = 5\text{mA}$			0.5	V
I_{OFF}	OFF-State Current	$V_O = 5\text{V}$ $V_O = 3.3\text{V}$			1	μA

Note 1: Pulse testing techniques maintain junction temperature close to ambient temperature; thermal effect must be taken into account separately.

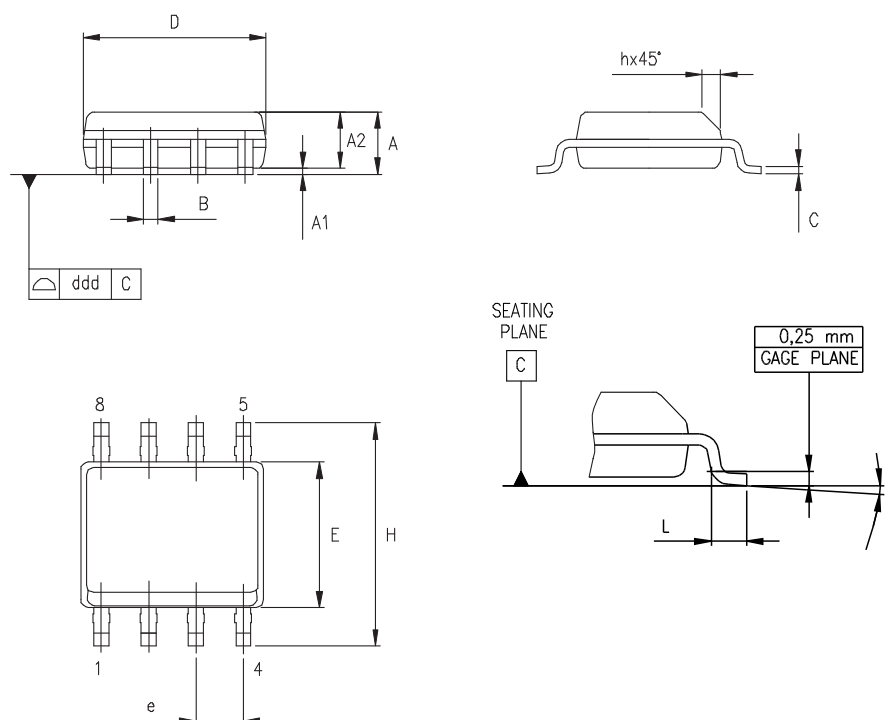
Note 2: Specified by design, not production tested.

TEST CIRCUIT

WAVEFORM: PROPAGATION DELAYS ($f=1\text{MHz}$; 50% duty cycle)

SO-8 MECHANICAL DATA

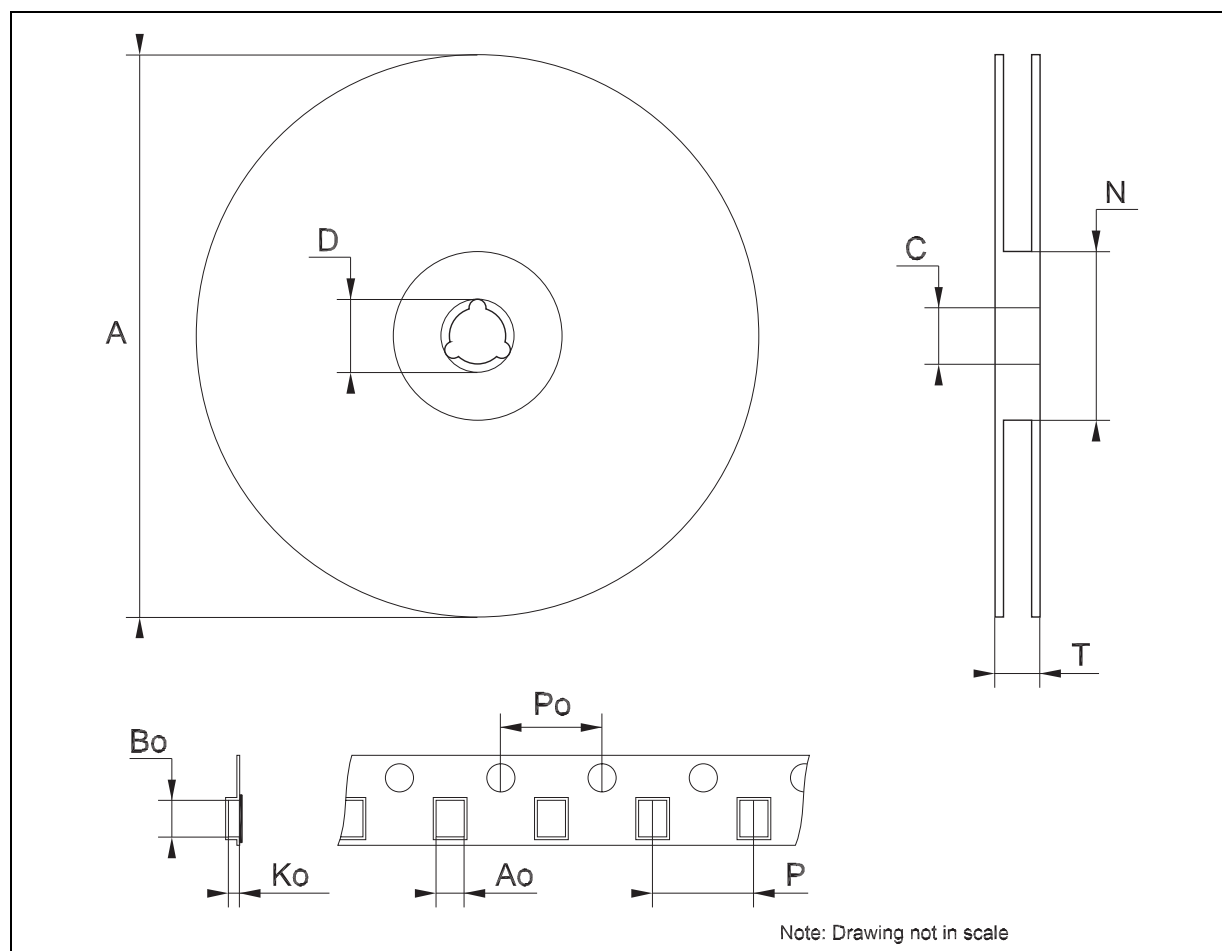
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	1.35		1.75	0.053		0.069
A1	0.10		0.25	0.04		0.010
A2	1.10		1.65	0.043		0.065
B	0.33		0.51	0.013		0.020
C	0.19		0.25	0.007		0.010
D	4.80		5.00	0.189		0.197
E	3.80		4.00	0.150		0.157
e		1.27			0.050	
H	5.80		6.20	0.228		0.244
h	0.25		0.50	0.010		0.020
L	0.40		1.27	0.016		0.050
k	g° (max.)					
ddd			0.1			0.04



0016023/C

Tape & Reel SO-8 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			330			12.992
C	12.8		13.2	0.504		0.519
D	20.2			0.795		
N	60			2.362		
T			22.4			0.882
Ao	8.1		8.5	0.319		0.335
Bo	5.5		5.9	0.216		0.232
Ko	2.1		2.3	0.082		0.090
Po	3.9		4.1	0.153		0.161
P	7.9		8.1	0.311		0.319



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